

Vishay Siliconix

Automotive N-Channel 100 V (D-S) 175 °C MOSFET

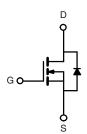
PRODUCT SUMMARY					
V _{DS} (V)	100				
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.025				
$R_{DS(on)} (\Omega)$ at $V_{GS} = 4.5 V$	0.029				
I _D (A)	40				
Configuration	Single				
Package	TO-252				



FEATURES

- TrenchFET[®] power MOSFET
- · Package with low thermal resistance
- 100 % $\rm R_g$ and UIS tested
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C = 25 \text{ °C}$, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V _{DS}	100	M	
Gate-Source Voltage	V _{GS}	± 20	V		
Continuous Drain Current	$T_C = 25 \ ^\circ C \ ^a$	Ŀ	40		
Continuous Drain Current	T _C = 125 °C	· I _D	26	A	
Continuous Source Current (Diode Conductio	n) ^a	I _S	40		
Pulsed Drain Current ^b	I _{DM}	160			
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	40		
Single Pulse Avalanche Energy	L = 0.1 mm	E _{AS}	80	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	Pn	136	W	
	T _C = 125 °C	гD	45	vv	
Operating Junction and Storage Temperature	T _J , T _{stg}	-55 to +175	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	50	°C/W	
Junction-to-Case (Drain)		R _{thJC}	1.1	0/10	

Notes

a. Package limited.

b. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

c. When mounted on 1" square PCB (FR4 material).



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static	•				•	•		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 V, I_D = 250 \mu A$		100	-	-	v	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	V _{DS} = V _{GS} , I _D = 250 μA		-	2.5	v	
Gate-Source Leakage	I _{GSS}	V _{DS} =	$0 \text{ V}, \text{V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 100 V	-	-	1.0		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 100 V, T _J = 125 °C	-	-	50	μA	
		$V_{GS} = 0 V$	V _{DS} = 100 V, T _J = 175 °C	-	-	250		
On-State Drain Current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	50	-	-	Α	
		V _{GS} = 10 V	I _D = 40 A	-	0.019	0.025	Ω	
Drain-Source On-State Resistance ^a	D D	$V_{GS} = 10 V$	I _D = 40 A, T _J = 125 °C	-	-	0.050		
Drain-Source On-State Resistance "	R _{DS(on)}	V _{GS} = 10 V	I _D = 40 A, T _J = 175 °C	-	-	0.063		
		V _{GS} = 4.5 V	I _D = 20 A	-	0.021	0.029		
Forward Transconductance b	g fs	V _{DS} = 15 V, I _D = 40 A		-	73	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}			-	2703	3380	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 25 V, f = 1 MHz	-	312	390		
Reverse Transfer Capacitance	C _{rss}			-	127	160		
Total Gate Charge ^c	Qg			-	46	70		
Gate-Source Charge ^c	Q _{gs}	$V_{GS} = 10 V$	$V_{DS} = 50 \text{ V}, I_D = 40 \text{ A}$	-	8.2	-	nC	
Gate-Drain Charge ^c	Q _{gd}			-	13	-	1	
Gate Resistance	Rg	f = 1 MHz		0.9	1.8	3.1	Ω	
Turn-On Delay Time ^c	t _{d(on)}	$V_{DD} = 50 \text{ V}, \text{ R}_{\text{L}} = 1.25 \Omega$ $\text{I}_{\text{D}} \cong 40 \text{ A}, \text{ V}_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$		-	11	17	ns	
Rise Time ^c	t _r			-	11	17		
Turn-Off Delay Time ^c	t _{d(off)}			-	27	41		
Fall Time ^c	t _f			-	6	9		
Source-Drain Diode Ratings and Chara	cteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	160	A	
Forward Voltage	V _{SD}	$I_{\rm F} = 40 \text{ A}, V_{\rm GS} = 0 \text{ V}$		_	0.9	1.5	V	

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

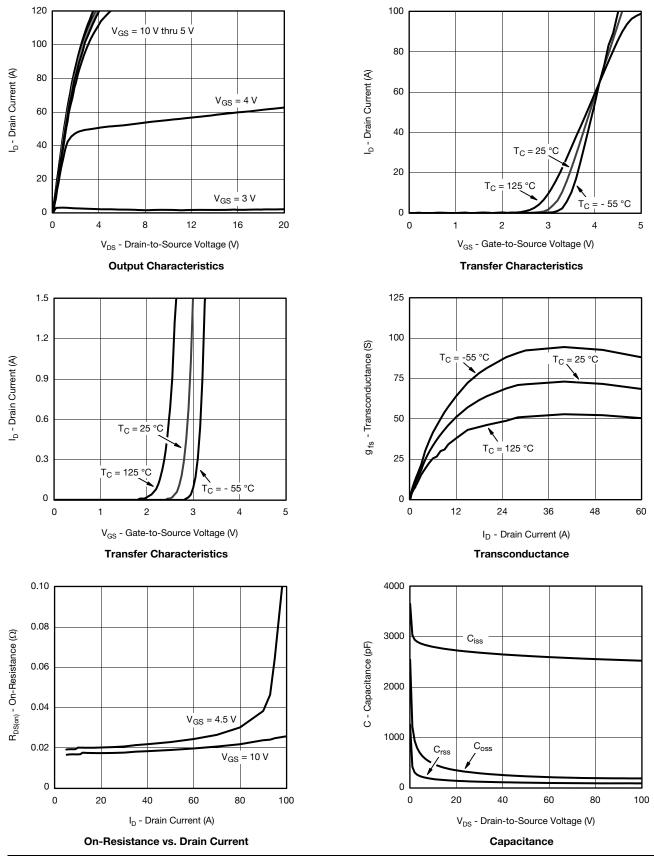
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SQD40N10-25

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TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



S15-1873-Rev. E, 10-Aug-15

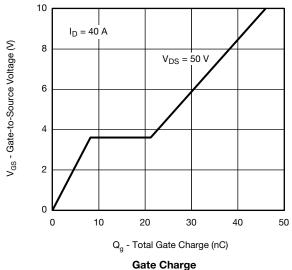
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Document Number: 69064

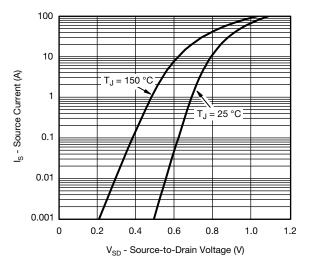
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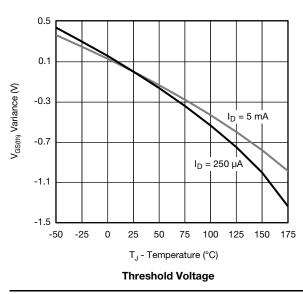
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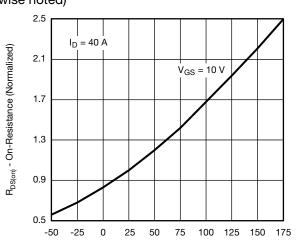


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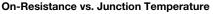


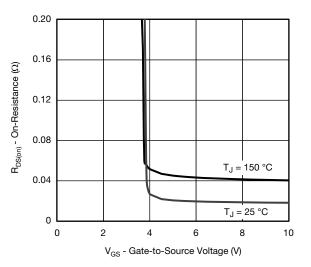
Source Drain Diode Forward Voltage



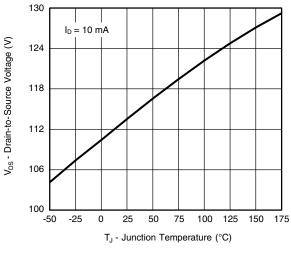


T_J - Junction Temperature (°C)









Drain Source Breakdown vs. Junction Temperature

S15-1873-Rev. E, 10-Aug-15

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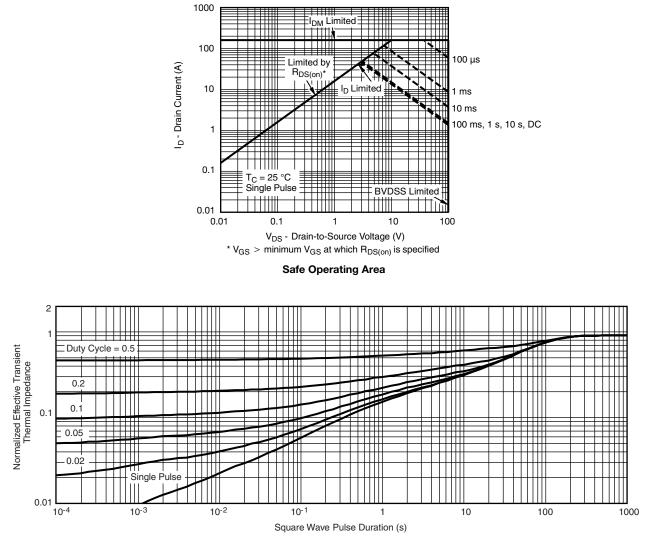
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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)

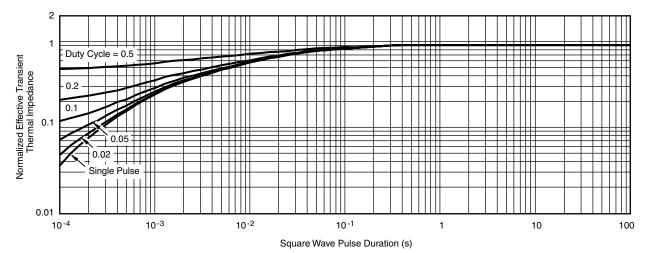


Normalized Thermal Transient Impedance, Junction-to-Ambient



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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- Normalized Transient Thermal Impedance Junction to Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction to Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?69064.

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The characteristics shown in the two graphs



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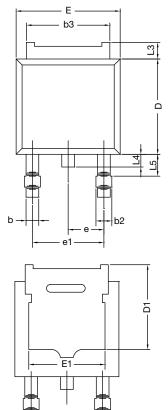
REVISION	HISTORY ^a	
REVISION	DATE	DESCRIPTION OF CHANGE
E	04-Aug-15	Revised R _g minimum limit

Note

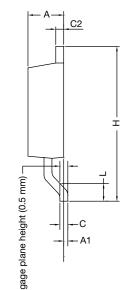
a. As of April 2014



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TO-252AA Case Outline



	MILLIMETERS		INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
А	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28 BSC		0.090 BSC		
e1	4.56	BSC	0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T13-0592-Rev. A, 02-Sep-13 DWG: 6019					

Note

• Dimension L3 is for reference only.

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RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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